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High-Performance Negative Self-Powered α -MoO₃/Ir/ α -MoO₃ Photodetectors: Probing the Influence of Coulomb Deep Traps

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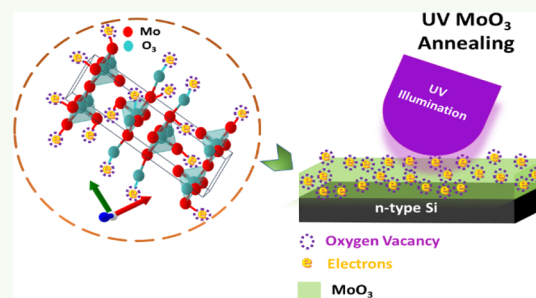
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ABSTRACT: Nanostructures of ultrathin 2D MoO₃ semiconductors have gained significant attention in the field of transparent optoelectronics and nanophotonics due to their exceptional responsiveness. In this study, we investigate self-powered α -MoO₃/Ir/ α -MoO₃ photodetectors, focusing on the influence of induced hot electrons in ultrathin α -MoO₃ when combined with an ultrathin Ir plasmonic layer. Our results reveal the presence of both positive and negative photoconductivity at a 0 V bias voltage. Notably, by integrating a 2 nm Ir layer between post-annealed α -MoO₃ films, we achieve remarkable performance metrics, including a high I_{ON}/I_{OFF} ratio of 3.8×10^6 , external quantum efficiency of 132, and detectivity of 3.4×10^{11} Jones at 0 V bias. Furthermore, the response time is impressively short, with only 0.2 ms, supported by an exceptionally low MoO₃ surface roughness of 0.1 nm. The observed negative photoresponse is attributed to O₂ desorption from the MoO₃ surface, resulting in increased carrier density and reduced mobility in the Ir layer due to Coulomb trapping and oxygen vacancy deep levels. Consequently, this leads to a decreased carrier mobility and diminished current in the heterostructure. Our findings underscore the enormous potential of ultrathin MoO₃ semiconductors for high-performance negative conductivity optoelectronics and photonic applications.

KEYWORDS: MoO₃, iridium, plasmonics photodetectors, negative photoconductivity (NPC), atomic layer deposition (ALD)



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INTRODUCTION

In a semiconductor, the conductivity is determined by the movement of charge carriers, which are typically electrons and “holes” (positively charged vacancies left behind when electrons move). The conductivity of a semiconductor can be influenced by external factors like temperature, applied electric fields, and the presence of impurities or other materials.¹ Intrinsic photoconductivity primarily involves transitions of electrons from the valence band to the conduction band, driven by the absorption of light, while extrinsic photoconductivity involves charge carrier generation associated with impurity energy levels introduced through doping or defects in the semiconductor material. Both intrinsic and extrinsic photoconductivity play important roles in the behavior of semiconductors under light exposure and are crucial for various optoelectronic applications, such as solar cells, photodetectors, and imaging sensors.

Positive photoconductivity (PPC) refers to the increase in the conductivity that occurs when a semiconductor is illuminated. Conversely, negative photoconductivity (NPC) occurs when the conductivity decreases under illumination. The phenomenon of NPC has been detected in different semiconductor materials, and numerous theoretical models have been suggested in scientific literature to elucidate the underlying mechanism.^{2–11} NPC can be attributed to the existence of an intense nonequilibrium electron distribution in the CB upon monoenergetic excitation. Under such circumstances, the

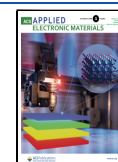
lifetime of electrons in the CB is shorter than the relaxation time resulting from acoustic phonon scattering. As a consequence, when the energy of the photogenerated electrons is a multiple of the longitudinal optical phonon energy, the photocurrent generated flows in the opposite direction to the electric field.⁶ The causes of NPC in various materials are diverse and can be attributed to different factors. These include the formation of scattering centers,^{12,13} deep defect levels,¹⁴ water adsorption,¹⁵ surface plasmon resonance,¹⁶ charge carrier trapping,¹⁷ and donor atom-like centers,¹⁸ among others. Some other possible reasons are the generation of secondary hot electrons,^{12,13} the trionic effect,¹⁹ the formation of the built-in electric field,^{20,21} light-activated trap states,²² thermal broadening of electron distribution,⁶ and intraband scattering.²³ However, despite numerous studies, there is still no clear consensus on the fundamental cause of this phenomenon.

In a study by Yang et al.,²⁴ they observed NPC in a MoO₃ nanoflakes/graphene heterocomposite under red light irradiation. The current flowing through the sample decreased to 10%

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of its original value when exposed to red light, indicating an approximately 10-fold increase in resistance. The resistance recovery process took over 500 s, suggesting that restoring the original resistance was more challenging than the resistance increase. This negative photoconductivity behavior demonstrated the ability to control the resistance of the heterocomposite using red light irradiation, highlighting its potential for photoresponsive applications. In principle, both NPC and PPC could be observed in some materials under different conditions. PbTe, a well-studied semiconductor, exhibits both PPT and NPC. Introducing elements like Ga and Eu in the doping process of p-type $\text{Pb}_{1-x}\text{Eu}_x\text{Te}$ films triggers a transition from negative to positive photoconductivity. The disorder caused by Eu atoms leads to a metal–insulator transition known as the Anderson transition. The behavior is influenced by the position of the 4f level, and under illumination, positive photoconductivity arises from the involvement of the 4f level, while negative photoconductivity arises from defect levels within the energy gap.²⁵ In a separate investigation carried out by Grillo et al.,²⁶ both NPC and PPC were identified in PtSe_2 field-effect transistors. The researchers observed that the transition from PPC to NPC is contingent on environmental pressure. The pressure-dependent behavior of photoconductivity suggests that the adsorption and desorption of air molecules significantly influence the charge transport. When the light source is deactivated, an excess of electron–hole recombination induces a decrease in current, followed by a gradual increase in current due to the readsorption of oxygen on the surface of PtSe_2 . By comprehending the charge transfer dynamics between physisorbed oxygen molecules and the PtSe_2 layer, a novel avenue emerges for controlling carrier density and the optical properties of the material.²⁷

NPC devices have a wide range of potential applications. They can be used in photodetection and imaging, allowing for highly sensitive imaging under low-light conditions, night vision technology, and improved astronomical observations. NPC devices also serve as optoelectronic switches. This makes them useful in optical communication systems, where fast data transmission is required. In the field of photovoltaics, NPC materials can be integrated into solar cells to enhance efficiency by reducing power losses under intense light. Additionally, NPC devices can be utilized as light sensors or light-dependent resistors (LDRs). They have applications in automatic brightness control for displays, adaptive street lighting, and proximity sensors. Lastly, NPC materials show promise in optical memory devices, enabling the storage and retrieval of data using light. Qin et al. and Zhuang et al. have demonstrated the use of NPC in nanodiamonds and applied it to high-sensitivity carbon-based humidity sensors.^{28,29} Hassan et al. observed NPC in HfO_x thin films and used it for visible light sensors.³⁰ Similarly, Singh et al. utilized the NPC concept for CuSe photodetector (PD) and achieved a sensitivity of 618 A/W under low bias.³¹ Moreover, the NPC phenomenon has been applied in ultrasensitive PD applications, including $\text{Cr}_2\text{Ge}_2\text{Te}_6$ and $\text{Cs}_3\text{Bi}_2\text{Cl}_9$ single crystals-based PD.^{21,32} These detectors showed high responsivity and on–off ratios. Additionally, NPC can be used for space exploration as doped semiconductors can exhibit ultrasensitive NPC, and the detection wavelength can be tuned in the infrared region by using different dopants.^{29,33} Overall, NPC devices have diverse applications and offer exciting possibilities for various technological advancements.

Gibbs free energy of IrO_2 is reported before,³⁴ it is worth noting that 1T- IrO_2 exhibits remarkable durability, with minimal

degradation even after undergoing an exhaustive 126 h chronopotentiometry measurement under the demanding conditions of a high current density of 250 mA/cm² within a proton exchange membrane device. This impressive resilience underscores its potential for enduring high-performance applications. Thus, IrO_2 stands out as the sole recognized catalyst for the oxygen evolution reaction (OER) that possesses a combination of remarkable catalytic activity and enduring stability in acidic environments.³⁵ This study investigates the integration of ultrathin plasmonic Ir films (1, 2, and 4 nm) within a MoO_3 – MoO_3 sandwich structure on a Silicon substrate. Post-annealing processes are applied to the samples. Optoelectronic properties under UV illumination and at 0 V bias conditions will be examined for self-powered UV PD. Hall effect measurements will determine carrier concentration and mobility, indicating performance factors such as responsivity (P_g), detectivity (D^*), external quantum efficiency (EQE), and OFF-ON responses. Overall, these findings demonstrate the potential of using nanostructured MoO_3/Ir heterostructures for high-performance self-powered PDs. By understanding the underlying mechanisms governing optoelectronic behaviors and the role of specific layers, we can further optimize the design and performance of these devices. The study will also analyze the influence of the plasmonic Ir layer on electron/hole concentrations and provide insights into the observed negative photoconductivity phenomena.

■ MATERIALS AND METHODS

Preparing the Ultrathin MoO_3 Film. A 2D α - MoO_3 film was synthesized on a 1 cm² n-type Si substrate by using an ALD system. To activate the substrate surface, an O_2 plasma cleaner was employed for 1 min. Subsequently, the substrate was placed in the ALD chamber for the growth of the MoO_3 thin film using the ANRIC Technologies brand (AT410) ALD system. For the deposition process, a Mo-based organometallic precursor material, bis(*t*-butylimido)bis(dimethylamino)molybdenum(VI), was introduced onto the substrate surface within an argon atmosphere of 99.999% purity, with a flow rate of 20 sccm, under a low pressure of approximately 0.3 Torr. The amount of precursor material deposited was controlled by adjusting the open time of the valve between the growth chamber and the precursor material chamber as well as the temperature of the growth chamber and the controlled heating of the precursor material chamber (~80 °C). To prevent condensation between the growth chamber and the material chamber, the pipes were maintained at 100 °C, while the outlet manifold was kept at 105 °C. In the subsequent stage, the gases released during deposition on the substrate were expelled from the growth chamber at a flow rate of 10 sccm. In the third stage, the controlled introduction of O_3 into the growth chamber was facilitated using the ANRIC Technology ATO_3 module. This oxidation process transformed the organo-metallic layer into a single layer of a MoO_3 thin film. Finally, the residual gases were evacuated to complete the cycle. Previous research has demonstrated that depositing MoO_3 samples at 200 °C yields favorable results for optoelectronic and electronic applications.²⁵

Ultrathin Ir Layer. To achieve an ultrathin layer of Ir with a thickness of just a few nanometers, a Leica EM ACE600 US sputter coater was utilized. The objective was to examine the influence of Ir, so layers with thicknesses of 1, 2, and 4 nm were deposited while maintaining a constant thickness for the MoO_3 layer. The deposition took place on a high vacuum film surface under a pressure of 1×10^{-3} mbar. The deposition process involved the use of Ar plasma with a depositing pressure of 5.0×10^{-2} mbar and an applied current of approximately 50 mA. To monitor the thickness, a quartz thickness monitor was employed. The sputtering rate for all of the samples remained consistent at 0.06 nm/s. However, to enhance the crystallinity of the thin films and achieve the α - MoO_3 phase, it is advisable to subject the deposited MoO_3/Si to annealing in a tube furnace at 600 °C for 15

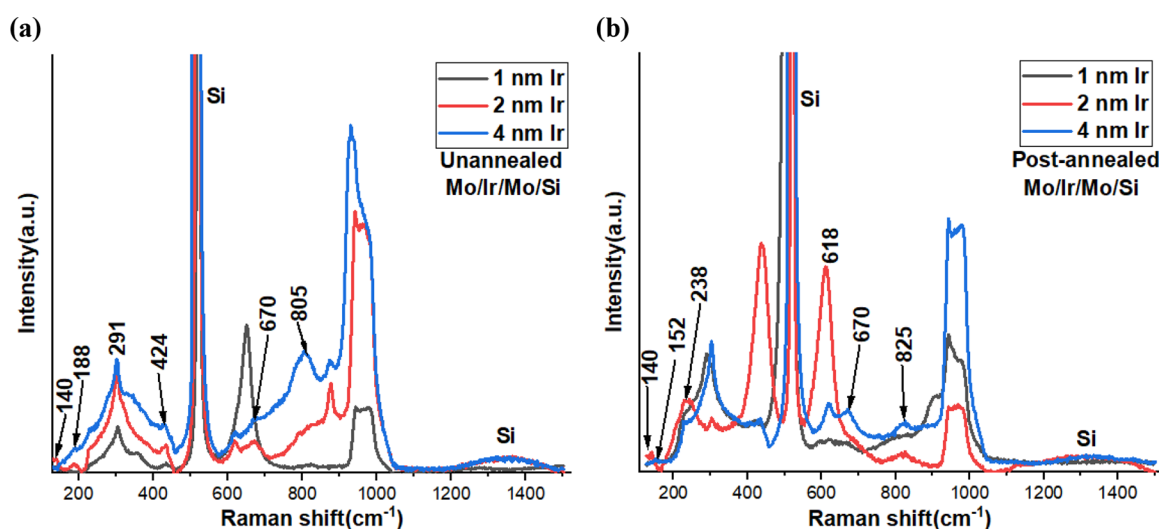


Figure 1. Raman spectroscopy analysis of unannealed (a) and post-annealed (b) MoO₃/Ir/MoO₃/Si with different thicknesses of the Ir layer of 1, 2, and 4 nm.

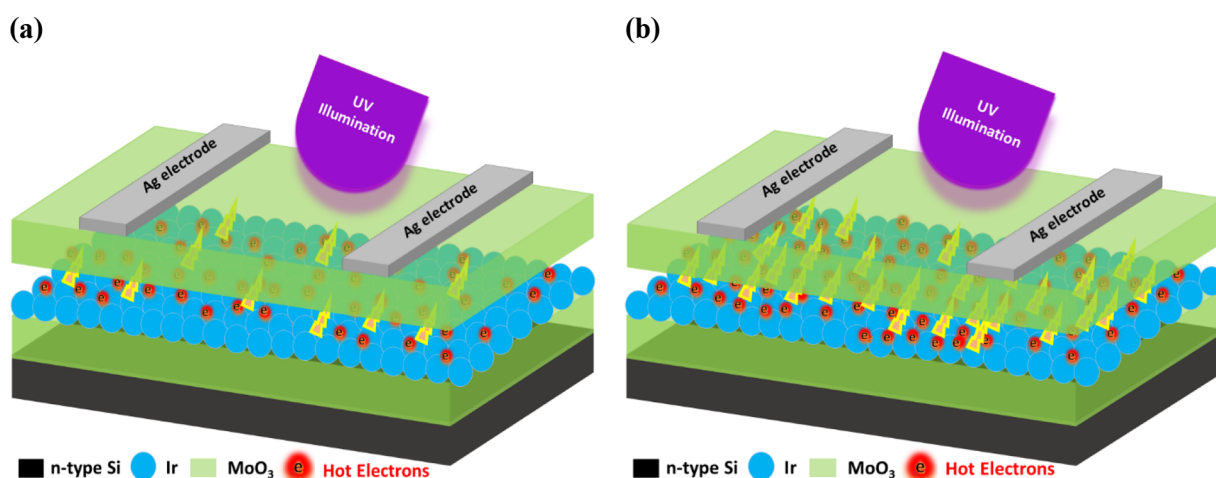


Figure 2. Schematic diagram for both unannealed (a) and post-annealed (b) samples under UV illumination.

min within an ambient air environment.^{36,37} Following the annealing process, the Ir layer is deposited followed by the upper MoO₃ layer. For the unannealed samples, only the first MoO₃ layer was annealed, while the upper MoO₃ layer did not undergo annealing. In contrast, for the post-annealed samples, both the upper and lower MoO₃ layers received annealing under the same conditions.

Characterization Methods. A variety of characterization techniques were employed to understand the properties of the thin films. The surface morphology was analyzed by using a field-emission scanning electron microscope (FESEM) Zeiss Gemini 500, while energy-dispersive X-ray spectroscopy (EDS) was used to identify the elemental composition of the films. Atomic force microscopy (AFM) Park XE7 system was used to investigate the topography and line profile spectrum, and Raman spectroscopy of $\lambda = 532$ nm was used to study the crystallinity and identify the 2D α -MoO₃ phase. Electrical properties, including carrier concentration and mobility, were measured by using the SWIN Hall8800 Hall effect measurement system. Electrical I–V and optoelectronic measurements were performed by using a Sourcemeater and a four-probe system. The illumination source had a 365 nm UV wavelength. Finally, the thickness of the films was measured by using the FILMETRIC F20–UV thin film analyzer. The opportunity to analyze the diffuse reflectance (*R*) spectra of our prepared samples within the 200–700 nm range was facilitated by employing UV–vis-NIR Spectroscopy (UV-3600Plus, Shimadzu).

RESULTS AND DISCUSSION

Identifying the 2D α -MoO₃ Phase Raman Analysis. For a better understanding of the phase changes in the postannealed samples, we did a Raman analysis for unannealed and postannealed samples and reported them in Figure 1. For the case of unannealed samples, it is seen that the main peak of 522 cm⁻¹ is related to Si.³⁸ Meanwhile, by coating Ir, the MoO₃ Raman shift peaks predominated. The peaks at 522, 424, and 825 cm⁻¹ are related to α -MoO₃. It can be seen that this shift to a higher Raman shift is related to the thickness of Ir under MoO₃ film.³⁸ The introduction of an Ir layer, being a plasmonic metal, can significantly influence the Raman peaks due to its ability to enhance light reflection compared with the MoO₃ oxide layer. While 618, 617, and 618 cm⁻¹ are associated with Si, 370 cm⁻¹ corresponds to the α -MoO₃. The peaks of 822, 825, and 824 cm⁻¹ could be related to Ir.³⁹ The peak at 1301 cm⁻¹ is related to Si. Here, due to using two layers of MoO₃ in between Ir one, we found some more peaks related to MoO₃ at around 152, 140, and 188 cm⁻¹, respectively, for 1, 2, and 4 nm Ir thickness cases. However, the peak at 725 cm⁻¹ might be related to Ir phase.⁴⁰ The peak at 816 cm⁻¹ is attributed to 2D α -MoO₃.^{41–43} Meanwhile, for the postannealed case, the Raman spectrum

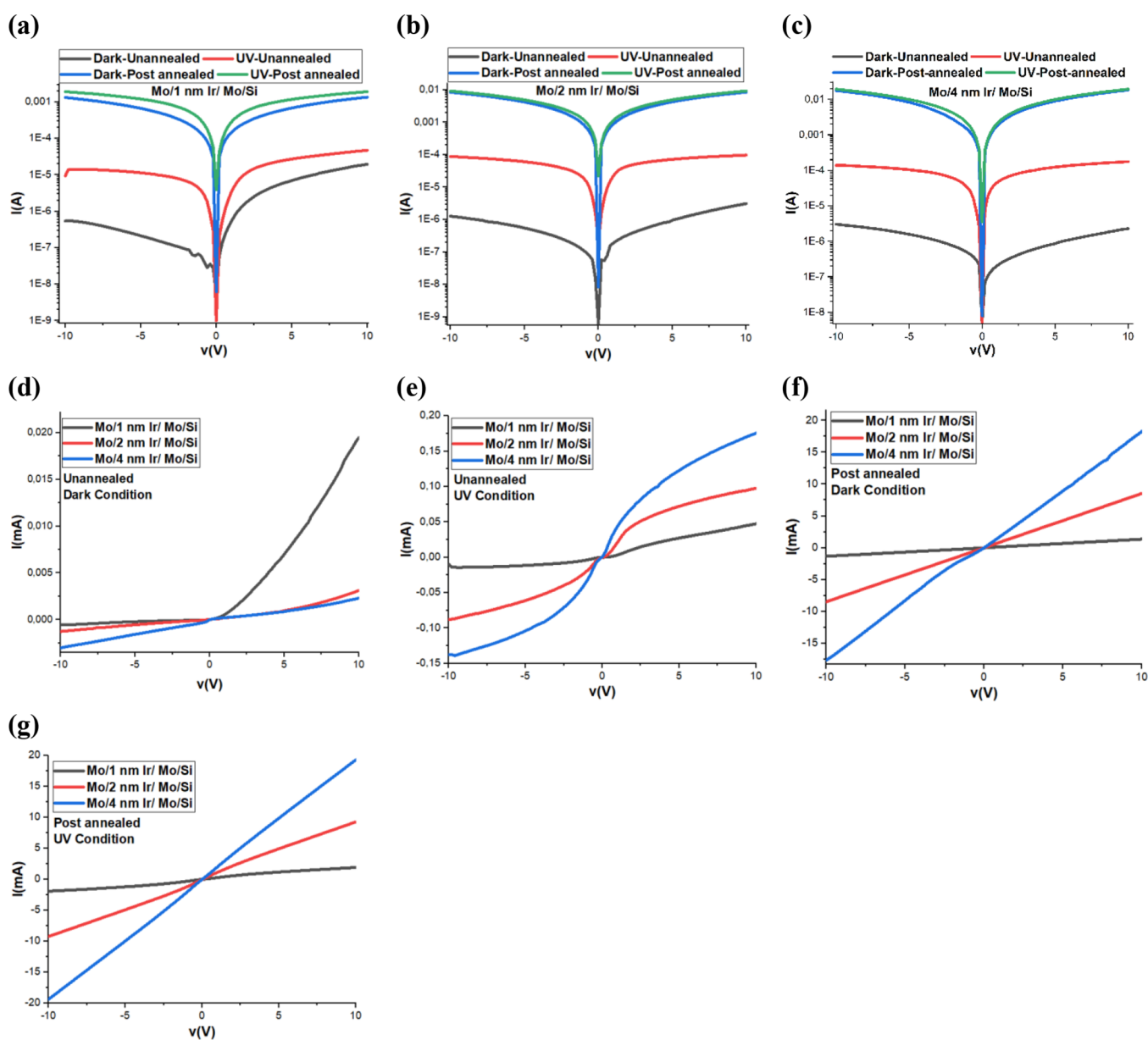


Figure 3. Log I - V curves of Mo/Ir/Mo/Si samples with different Ir layer thicknesses: 1 nm (a), 2 nm (b), and 4 nm (c), considering both unannealed and postannealed films. Additionally, linear I - V curves are provided for 1, 2, and 4 nm Ir thickness samples in both unannealed (d and e) and postannealed (f and g) states.

shows interesting results. For the $\text{MoO}_3/1 \text{ nm Ir/MoO}_3/\text{Si}$: 818 cm^{-1} is assigned to the A_{1g} mode,⁴⁴ and 291 and 669 cm^{-1} are assigned to the B_{2g} mode.⁴⁴ These are related to the 2D α - MoO_3 behavior. For $\text{MoO}_3/2 \text{ nm Ir/MoO}_3/\text{Si}$: 823 cm^{-1} is assigned to the A_{1g} mode,⁴⁴ and 670 cm^{-1} is assigned to the B_{2g} mode,⁴⁴ which are also related to 2D α - MoO_3 behavior. The peak at 238 cm^{-1} corresponds to a nonstoichiometric MoO_{3-x} .⁴⁵ For $\text{MoO}_3/4 \text{ nm Ir/MoO}_3/\text{Si}$: 826 cm^{-1} is assigned to the A_{1g} mode,⁴⁴ and 672 cm^{-1} is assigned to the B_{2g} mode.⁴⁴ These peaks are related to 2D α - MoO_3 behavior. Ultimately, the postannealed $\text{MoO}_3/2 \text{ nm Ir/MoO}_3/\text{Si}$ sample exhibits heightened peak intensities, accompanied by intriguing peaks associated with the presence of a highly crystalline 2D α - MoO_3 film. This result could contribute to high optoelectronic performances and high carrier concentrations.

Current–Voltage Characteristics. The optoelectronic behavior under UV illuminations for both unannealed and

postannealed samples promises an excitation of the hot electrons on the surface of the Ir layer. For this purpose, a schematic diagram representing the concentration of the hot electrons for unannealed and postannealed cases is depicted in Figure 2.

The logarithmic IV curves are shown in Figure 3a–c. A discernible presence of a minor current near the origin point was evident across all samples regardless of the Ir thickness. This subtle current persisted uniformly, irrespective of variations in the material. However, the distinction between samples subjected to light exposure and those in darkness was noteworthy. When the samples were examined under unilluminated conditions, the dark current remained notably low. This indicated that in the absence of light, the current near the origin point exhibited stability. Conversely, in the presence of illumination, a significant alteration became apparent. The dark current, which was initially at a minimum, displayed a noticeable increase when exposed to light. This alteration

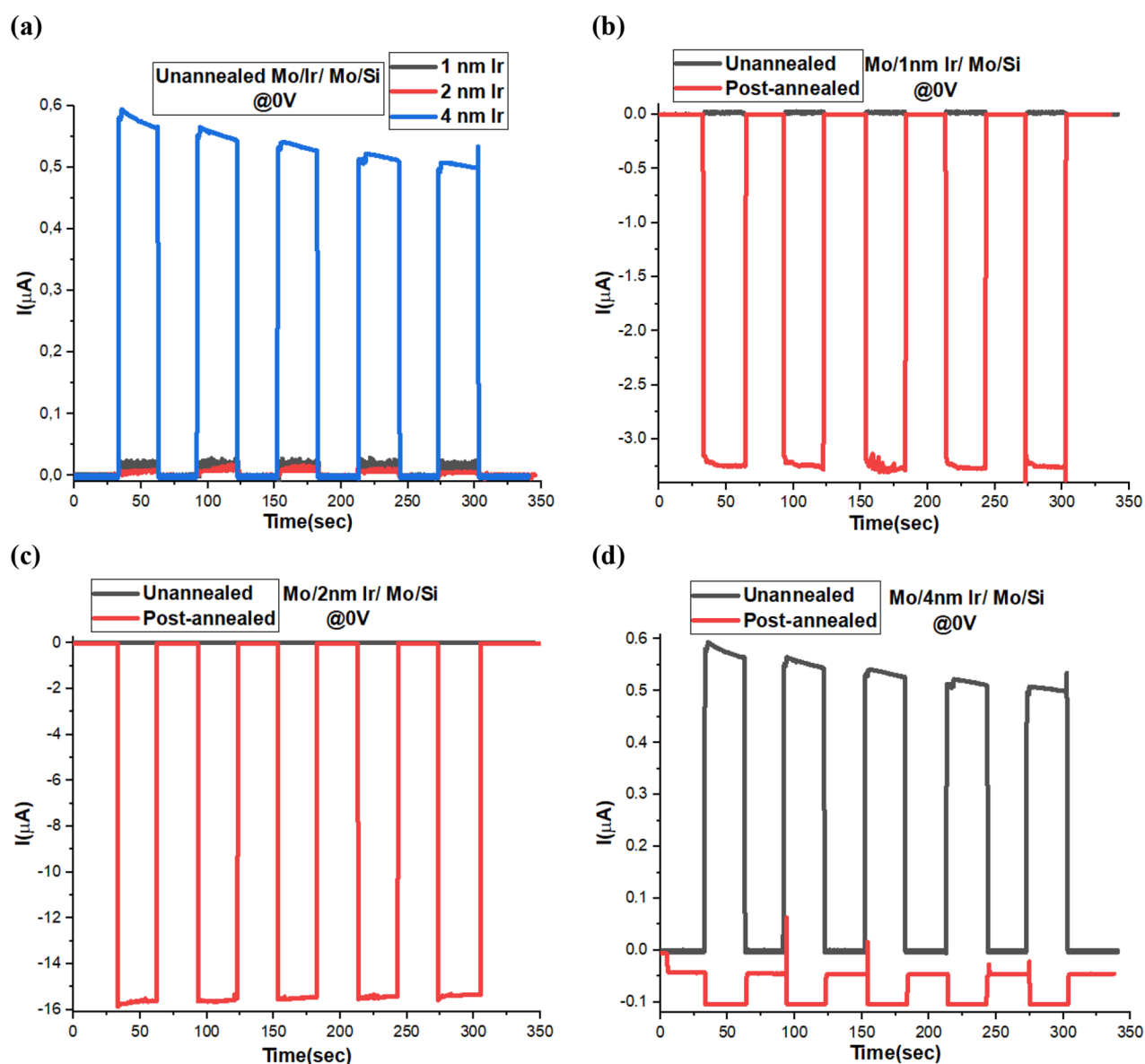


Figure 4. Illustrates the self-powered OFF-ON response of unannealed $\text{MoO}_3/\text{Ir}/\text{MoO}_3/\text{Si}$ samples with varying Ir layer thicknesses: 1, 2, and 4 nm (a). Additionally, the behavior of $\text{MoO}_3/\text{Ir}/\text{MoO}_3/\text{Si}$ samples for both unannealed and post-annealed conditions is shown for the 1 nm Ir layer (b), 2 nm Ir layer (c), and 4 nm Ir layer (d), all under zero voltage bias.

indicated that the introduction of light triggered a distinct shift in the current behavior near the origin point. This transformation likely stems from the interaction between the incident light and the inherent properties of the material, leading to adjustments in the electrically conductive attributes of the samples.

Due to the significant difference in intensity between the levels of dark and ultraviolet (UV) illumination, we decided to improve the representation of the data. To achieve this, separate plots for each illumination condition are created, as illustrated in Figure 3d–g. Upon analysis of these plots, a noticeable observation is that the unannealed samples, under both dark and illuminated conditions, exhibit behavior that deviates from what is known as Ohmic behavior. This outcome was somewhat anticipated due to the quality of MoO_3 present on the surface. The rectification was found to be highest for the $\text{MoO}_3/4\text{ nm Ir}/\text{MoO}_3/\text{Si}$ sample, generating a photocurrent of 20,000 μA at 10 V followed by the $\text{MoO}_3/2\text{ nm Ir}/\text{MoO}_3/\text{Si}$ sample, which

generated a photocurrent of 10,000 μA at 10 V. The $\text{MoO}_3/1\text{ nm Ir}/\text{MoO}_3/\text{Si}$ sample showed the lowest generated photocurrent of 2000 μA at 10 V. It is important to note that the I – V curves were found to be free from noise and disturbances under all measurements. Furthermore, a comparison between the unannealed and postannealed samples for the $\text{MoO}_3/\text{Ir}/\text{MoO}_3/\text{Si}$ group revealed that the post-annealed samples exhibited enhanced photocurrent. This material's crystalline structure is not highly developed, leading to the formation of what is referred to as Schottky behavior when in contact with Ag contacts. However, after subjecting the samples to an annealing process, significant improvements. This annealing process directly enhances the grain structure on the surface and promotes the growth of higher-quality crystals. Consequently, this refinement of the material's structure leads to a transformation in its behavior. Specifically, the transport properties are enhanced and the overall conductivity of the final device is increased. This suggests that the annealing process plays a

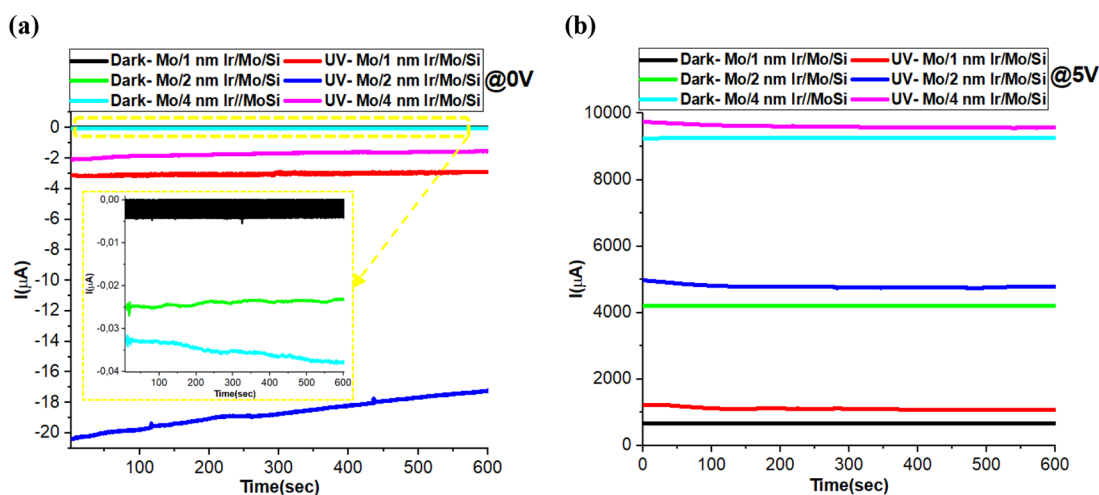


Figure 5. Temporal stability of MoO₃/Ir/MoO₃/Si PDs under dark and UV illuminations with varying 1, 2, and 4 nm Ir thickness and a bias voltage of 0 (a) and 5 V (b).

crucial role in optimizing the performance of the device by improving the material's properties, resulting in improved electrical conductivity.

UV Photodetector Performances. The study explores how the presence of different thicknesses of the Ir layer (1, 2, and 4 nm) affects the OFF-ON behavior of the thin film structure. The OFF-ON behavior refers to how well the thin film structure responds under dark and UV illuminations at 0 V for both groups of unannealed and post-annealed MoO₃/Ir/MoO₃/Si, as shown in Figure 4.

In Figure 4a, it can be seen that the positive photoresponses of the unannealed samples are limited to 0.6 μA under UV illumination at a 0 V bias. The 4 nm Ir sample exhibits the highest photocurrent, while the 1 and 2 nm Ir samples have the lowest with a small difference of less than 0.05 μA . Moreover, these curves exhibit excellent response dynamics during OFF-ON conditions. To investigate the impact of annealing on photoresponses, we compared the unannealed and postannealed samples in each group of 1, 2, and 4 nm Ir layers as in Figure 4b–d. In the case of 1 nm Ir, we observed a significantly higher negative photocurrent in the postannealed samples, reaching 3.5 μA , whereas the unannealed samples exhibited only a small photocurrent. Similarly, for the 2 nm Ir samples, the negative photocurrent in the postannealed samples increased to 16 μA . On the other hand, the 4 nm Ir sample showed a negative photocurrent of only 0.1 μA and poor dynamic behavior compared to the 1 and 2 nm samples. Interestingly, the 2 nm Ir sample showed the highest photocurrent under negative photocurrent behavior, while the 4 nm Ir sample exhibited the lowest. Overall, we observed an inverse relationship between the positive and negative photocurrent behaviors of the unannealed and postannealed samples, with higher negative photocurrents. These results show that 1 and 2 nm Ir are more interesting for enhanced plasmonic effects.

In addition, for checking the performance under higher voltages (0.5–5 V) and comparing it with 0 V performances, Figure S1 (Supporting Information) depicts the performance characteristics of unannealed and post-annealed MoO₃/Ir/MoO₃/Si devices with varying thicknesses of 1, 2, and 4 nm for the Ir layers under different applied bias voltages ranging from 0 to 5 V. The results show that despite the differences between the unannealed and post-annealed samples, both groups demonstrate well-defined OFF-ON responses with fast response and

recovery behaviors. This suggests that regardless of the annealing condition, the devices exhibit reliable and efficient switching characteristics. These results are inconsistent with diffuse reflectance (R) measurements as in Figure S3 (Supporting Information). R reveals an absorption peak around 365 nm, which slightly shifts toward longer wavelengths with increasing thickness.

Temporal Stability under 0 V. The performance of PDs cannot be solely determined from the I – V curves recorded at higher voltages. To obtain a better understanding of their capabilities, this study aimed to investigate the temporal stability of a specific type of PD composed of MoO₃/Ir/MoO₃/Si layers with varying thicknesses of Ir (1, 2, and 4 nm) under 0 V bias. The PD was subjected to both darkness and UV light and powered with 0 and 5 V, as in Figure 5, to evaluate its stability over time. The results of this study have the potential to enhance our comprehension of designing and utilizing PDs in fields such as optoelectronics and photonics. The PDs' temporal stability was analyzed by measuring their response to UV light and darkness over a period. At 0 V bias, all samples of the PD exhibited negative photoresponses, which were stable for a long time. The sample with a 2 nm thick Ir layer demonstrated the highest photocurrent of 20 μA , followed by the 1 nm Ir layer, which exhibited a photocurrent of 3 μA . In contrast, the sample with a 4 nm Ir layer showed a very low photocurrent of 2 μA . These findings suggest that thinner films of 1 and 2 nm Ir layers can potentially excite more hot electrons than thicker films of 4 nm, which may have implications in the development of more sensitive and efficient PDs for optoelectronics and photonics applications. These results confirm that ultrathin films of 1 and 2 nm Ir layers have the potential to excite more hot electrons than thicker films of 4 nm. This phenomenon could be attributed to the fact that thinner layers require less energy to generate hot electrons, which could contribute to the higher photocurrent observed in the samples with thinner Ir layers.

For the 5 V bias condition, it is apparent that the photocurrent increases as the Ir thickness increases. This suggests that a higher Ir content leads to a stronger response to UV illumination, resulting in a greater photocurrent. Therefore, the device's sensitivity to UV light improves with an increase in the thickness of the Ir layer. Additionally, the dark current of the photodetector varies with the Ir content. Among the samples, one with a 4 nm Ir layer exhibits the highest dark current value. This

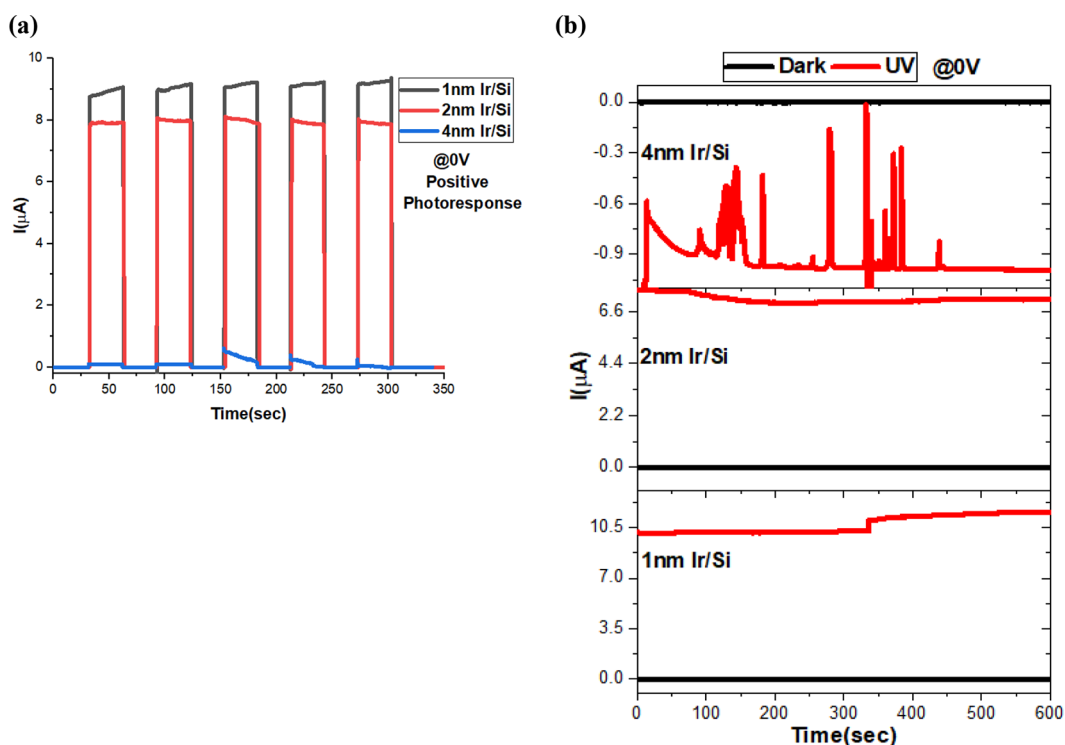


Figure 6. OFF-ON photoresponse (a) and transient response behavior under dark and UV illuminations (b) at 0 V of Ir/Si sample with different thicknesses of the Ir layer of 1, 2, and 4 nm.

implies that a thicker Ir layer contributes to a higher level of the dark current in the device. It is important to note that the dark current represents the current flowing through the device in the absence of any light stimulus, and a higher dark current can impact the overall performance and signal-to-noise ratio of the photodetector. Therefore, the findings suggest that thinner Ir layers could enhance the performance of PDs by improving their sensitivity and efficiency, which could have significant implications for various applications in optoelectronics and photonics.

Further investigations were conducted on the optoelectronic performance of Ir/Si structures with varying thicknesses of 1, 2, and 4 nm to gain a comprehensive understanding of the role of the Ir layer in the absence of MoO_3 layers. Figure 6 presents the results obtained from these investigations, shedding light on the underlying mechanisms behind the observed phenomena, such as the significantly reduced plasmonic behavior exhibited by the 4 nm Ir layer and the origin of the negative photocurrents observed in the $\text{MoO}_3/\text{Ir}/\text{MoO}_3/\text{Si}$ structures after the post-annealing process. Upon initial examination of the OFF-ON behaviors depicted in Figure 6a, it becomes apparent that the 1 and 2 nm Ir thickness conditions yield the highest photocurrents, exhibiting only minor differences with respect to each other under UV illuminations. Conversely, the 4 nm Ir thickness condition demonstrates the lowest photocurrent, displaying irregular patterns. It is important to note that the efficiency of hot carrier generation relies on various factors, including the thickness of the plasmonic layer. Generally, thinner plasmonic layers tend to generate a greater number of hot carriers compared to thicker layers, as elucidated elsewhere.⁴⁶ This can be attributed to the more efficient decay of surface plasmons in thinner layers, leading to a higher probability of hot carrier generation.

Furthermore, an interesting observation can be made regarding the behavior of the nanometer Ir layer over time, particularly it is very low photocurrents, as depicted in Figure 6b. This observation further reinforces the notion that the integration of the nm Ir layer is unsatisfactory for optoelectronic devices based on Ir. However, it is worth noting that both the 1 and 2 nm Ir layers exhibit comparable dark currents and demonstrate more stable photocurrents. These results corroborate the previous findings indicating that the 1 and 2 nm Ir layers yield the highest photoresponses, while the 4 nm Ir layer exhibits significantly lower photoresponses. Additionally, the Hall effect measurements of the Ir/Si device of 1, 2, and 4 nm thickness are depicted in Table S1 (Supporting Information). The results suggest that there is a higher density of charge carriers of $2.07 \times 10^{20} \text{ cm}^{-3}$ present in the 1 nm Ir layer compared to the others, 6.45×10^{19} and $5.48 \times 10^{17} \text{ cm}^{-3}$ for the 2 and 4 nm Ir layer, respectively. Of particular interest is the fact that these photoresponses, for all three thicknesses of Ir layers (1, 2, and 4 nm), are positive. This observation suggests that the Ir layer, regardless of its thickness, is not responsible for the negative photoresponses observed in the $\text{MoO}_3/\text{Ir}/\text{MoO}_3/\text{Si}$ structures. Instead, this strongly implies that the MoO_3 sandwich layers play a critical role in generating negative photoresponses. However, the case of postannealed 4 nm Ir/Si shows nonstability through time. This effect is similar to some reported studies, including the NPC phenomenon that was observed by Fu-Cheng Wang and colleagues in single quantum wells of InAs/AlSb that can be electrically resettable.⁴⁷ This is caused by the capture of photoexcited electrons through deep levels in AlSb, resulting in a decrease in the carrier density. A similar mechanism was also reported by Sadofyev et al. for NPC in the same system.⁴⁸

Hall Effect and Carrier Concentrations. The Hall effect measurements were performed at room temperature, and the

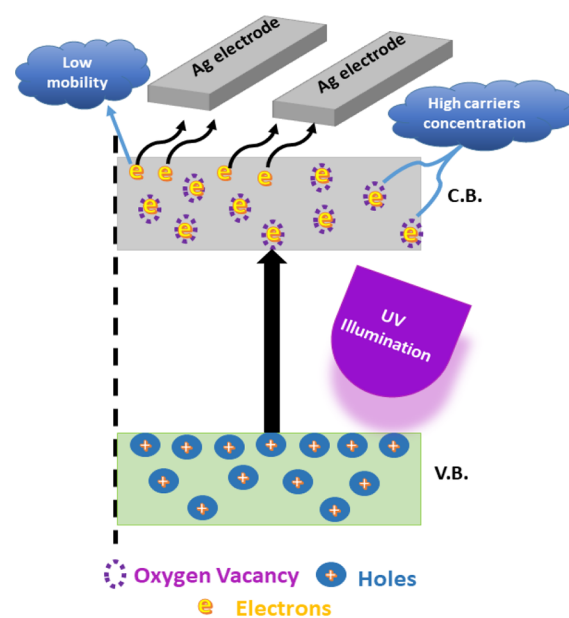
Table 1. Surface Sheet Resistance (R_s), Resistivity (R_{ho}), Hall Voltage (V_H), Hall Coefficient (R_H), Sheet Carrier Concentration (N_s/P_s), Carrier Concentration (N/P), and Mobility (Mob) for Both Unannealed and Post-annealed Samples

code	sample	R_s (ohm/sq)	R_{ho} (/ohm cm)	V_H (V)	R_H (m ³ /C)	type	N_s/P_s (/cm ²)	N (/cm ³)	mobility (cm ² / (V s))
unannealed	MoO ₃ /1 nm Ir/ MoO ₃ /Si	1.68×10^6	1.06×10^0	-6.98×10^{-3}	-6.13×10^{-5}	n	-6.45×10^{10}	-1.02×10^{17}	5.76×10^1
	MoO ₃ /2 nm Ir/ MoO ₃ /Si	5.25×10^5	3.80×10^{-1}	-7.75×10^{-3}	-2.59×10^{-4}	n	-1.74×10^{10}	-2.41×10^{16}	6.83×10^2
	MoO ₃ /4 nm Ir/ MoO ₃ /Si	5.66×10^4	5.31×10^{-2}	-1.45×10^{-2}	-3.77×10^{-5}	n	-1.55×10^{11}	-1.66×10^{17}	7.09×10^2
post-annealed	MoO ₃ /1 nm Ir/ MoO ₃ /Si	3.02×10^4	3.42×10^{-2}	-1.32×10^{-5}	-6.92×10^{-7}	n	-1.02×10^{13}	-9.02×10^{18}	2.02×10^1
	MoO ₃ /2 nm Ir/ MoO ₃ /Si	2.11×10^5	2.58×10^{-1}	2.41×10^{-5}	4.09×10^{-7}	p	1.87×10^{13}	1.52×10^{19}	1.58×10^0
	MoO ₃ /4 nm Ir/ MoO ₃ /Si	1.67×10^4	2.40×10^{-2}	-1.08×10^{-4}	-2.16×10^{-6}	n	-4.15×10^{12}	-2.89×10^{18}	8.99×10^1

recorded data are listed in Table 1. It was observed that the carrier concentrations directly correlated with the results obtained from the I - V measurements. Additionally, due to its highly conductive metallic nature, it was expected that Ir would exhibit significant carrier concentrations. On the other hand, the mobility of the carriers indicates how quickly electrons or holes move through the sample, specifically from the sample to the contacts. Essentially, the mobility factor reflects the sensitivity, detectability, and response characteristics (ON/OFF) of the samples, as reflected in the results. Another interesting observation is that thicker layers of Ir resulted in higher carrier concentrations, which can be attributed to the plasmonic properties of Ir as a metal, enabling the direct introduction of high carrier concentrations. In addition, it is known that plasmonic materials can induce more carrier concentrations (plasma frequencies) and faster carrier mobilities (plasmon damping constants).^{49,50}

Also, all samples present an n-type semiconducting behavior except for the post-annealed MoO₃/2 nm Ir/MoO₃/Si sample. It is noted that by passing the post-annealing process, carrier concentration (N/P) is enhanced due to the large enhancement in the film crystallinity and acquiring oxygen vacancies, which act as electron donor centers. However, the mobility seems not to be so high, and it is a bit inversely proportional to the N concentrations. In simple terms, when there are high carrier concentrations, this suggests that there is a large number of charge carriers available for transportation. However, because there are so many carriers nearby, they tend to interact with each other or with impurities and defects in the material. These interactions can cause the carriers to scatter or collide with defects (e.g., oxygen vacancies), making it harder for them to move freely. MoO₃ has been identified as a material with a significant number of oxygen vacancies.^{51,52} These vacancies could interact with the charge carriers present in the material, resulting in higher concentrations. When a large number of vacancies are involved, the higher carrier concentrations may hinder the smooth flow and ultimately reduce their mobility. In simpler terms, the interactions between the vacancies and carriers impede the carriers' ability to move freely, leading to lower mobility, as represented in Figure 7.

Negative Photoconductivity in MoO₃/Ir/MoO₃. The occurrence of both PPC and NPC has been observed in numerous materials and is influenced by several factors including light wavelength, intensity, applied bias voltage, relative humidity, temperature, and composition. The coexistence of PPC and NPC is not a universal phenomenon and varies depending on the specific conditions under which the

**Figure 7.** Schematic band gap diagram of the possible mechanism of carrier concentrations and the mobility as predicted from Hall effect measurements.

material is tested. For instance, in WO₃ nanowires,¹⁵ hybrid perovskite semiconductors,¹⁸ a mix of cubic zinc-blend and hexagonal wurtzite phases in III-V semiconductor nanowires,⁵³ p-type Pb_{1-x}Sn_xTe film,²⁵ single-layer graphene (SLG)-carbon nanotube thin film (CNTF) Schottky junction,⁵⁴ Pb/Sn perovskite,⁵⁵ CsPbX₃ (X = Cl, Br, or I) nanoheterojunctions,⁵⁶ bidoped hybrid halide perovskites octahedral semiconductors,⁵⁷ CsPbBr₃/graphene heterojunction,⁵⁸ Zn_{1-x}Cd_xO films,²⁷ graphene,⁵⁹ and 2D FePS₃.⁶⁰ In our case, the bias voltage well contributed to the positive and negative photocurrent. Several factors can contribute to the release of negative photoconductivity under light illumination, as previously mentioned. First, the photoresponse of only MoO₃/Si has been checked for understanding the role of the oxide layer. Figure 8 illustrates the MoO₃/Si OFF-ON photoresponses under UV illumination, providing valuable insights into the underlying factors responsible for the negative photoconductivity in MoO₃/Ir/MoO₃/Si. Notably, the deposition conditions for the MoO₃ layer closely resemble those of the MoO₃ layer in the MoO₃/Ir/MoO₃/Si structure. Additionally, both the MoO₃ layer in MoO₃/Ir/MoO₃/Si and the MoO₃/Si undergo postannealing processes, ensuring comparable conditions for deposition. Thus,

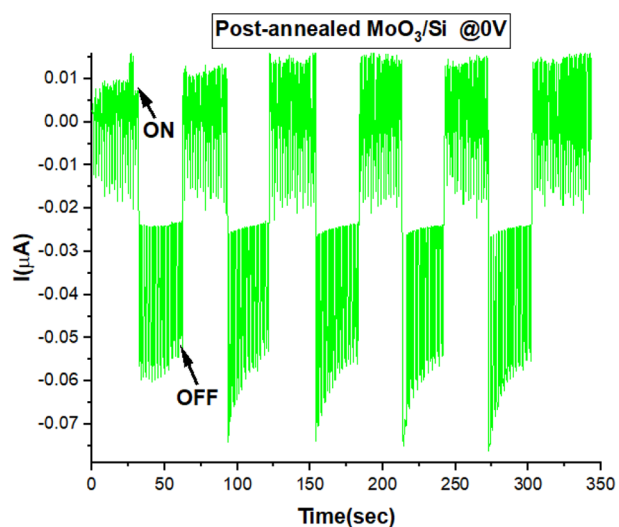
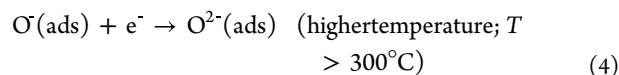
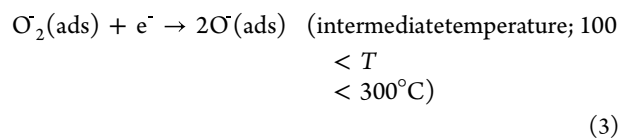
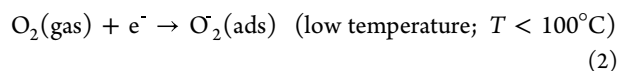


Figure 8. OFF-ON photoresponse of post-annealed MoO₃/Si under 0 V bias. It shows a negative photoresponse.

we can confidently assert that the MoO₃/Si and MoO₃/Ir/MoO₃/Si structures share the same deposition conditions. Through a thorough examination of the MoO₃/Si behavior, it is evident that it exhibits a negative photoresponse.

O₂ Adsorption/Desorption Mechanism., as shown in eqs 1–4.



The fact behind this is coming from the post-annealing process in an air environment at a bit high temperature. For the postannealed samples, under UV light irradiation, the MoO₃ ultrathin films undergo a process where some of the adsorbed O₂ molecules from the environment are desorbed from their surface.⁶¹ This releases electrons back to MoO₃, leading to an increase in its carrier density. As a result, the equilibrium between the Fermi levels of the MoO₃ and Ir layer is disrupted.⁶² Some of the released electrons move to the Ir layer and recombine with the holes in it, while some behave as Coulomb traps at the MoO₃/Ir interface. The latter quenches the holes of the Ir layer and lowers the hole mobility, which reduces the transport in the Ir layer. While the desorption of O₂ molecules from the surface of MoO₃ can contribute to an increase in the carrier density of MoO₃, not all of the liberated electrons are injected into the Ir layer or function as Coulomb traps. The increase in carrier density does enhance the transport properties of MoO₃ up to a certain threshold. However, due to the high carrier mobility of the Ir layer, the change in transport predominantly stems from the Ir layer rather than the entire heterostructure. Consequently, under light irradiation, the resistance of the heterostructure increases, resulting in a decrease in current. Additionally, in the absence of a post-annealing process, nearly all adsorbed O₂ molecules desorb, which accounts for the significantly higher resistance observed in the unannealed heterostructure compared to the post-annealed samples. Similar behavior has been reported in the previous

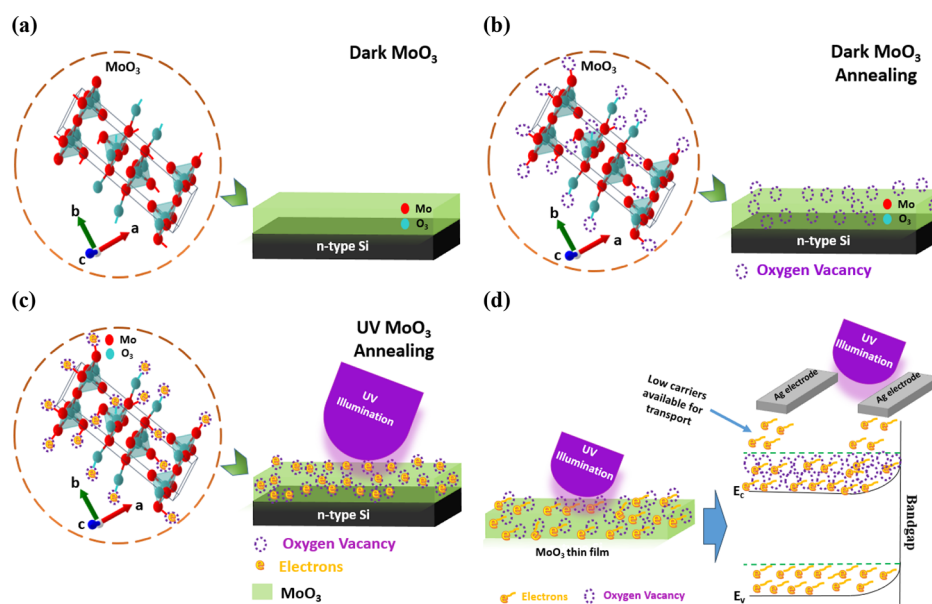


Figure 9. Schematic diagram depicting the potential process involved in the creation of oxygen vacancies responsible for the negative detector behavior on the surface of MoO₃. In the initial state, a nonannealed MoO₃ thin film is shown (a). Upon undergoing a post-annealing procedure in an air environment, the annealing process induces the formation of oxygen vacancies (b). Subsequently, upon exposure to light, the generated electrons occupy these oxygen vacancies, leading to an increase in carrier concentrations. However, this also results in a constraint on mobility (c). Consequently, the limited carrier mobility causes a reduced transfer to the metal contacts (d).

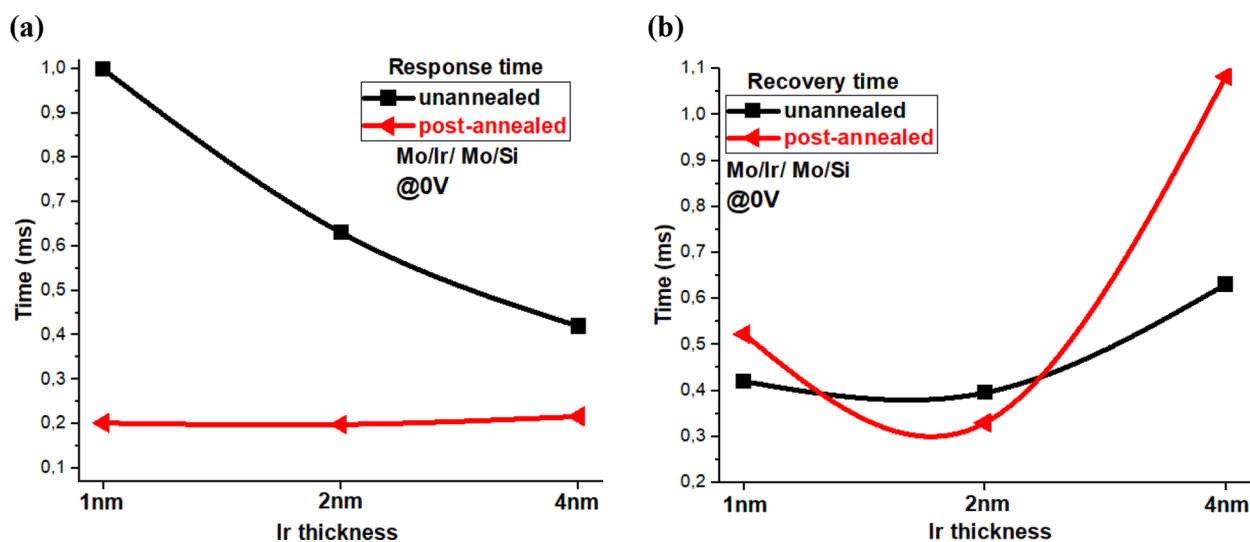


Figure 10. Response time (a) and recovery time (b) at 0 V voltage of unannealed and postannealed MoO₃/Ir/MoO₃/Si with different thicknesses of the Ir layer of 1, 2, and 4 nm.

literature.^{24,63} The generated photocurrent in our case is higher than that reported in MoO₃/graphene structures,²⁴ TiO₂-decorated graphene,⁶¹ and FePS₃ UV PD.⁶⁰

In contrast to the behavior observed under light irradiation, the absence of light resulted in the adsorption of some O₂ molecules onto the material's surface. These adsorbed molecules acted as traps for the electrons in MoO₃, forming anions and reducing the overall electron population in MoO₃. Consequently, the Fermi level of the material decreased. To maintain alignment between the Fermi level of MoO₃ and the Ir layer, the Fermi level of Ir also shifted downward. This shift caused an increase in the number of hole carriers within the Ir layer. Moreover, the decrease in the number of electrons in MoO₃ led to a reduction in the number of charge traps, resulting in an enhancement of the hole mobility within the Ir layer. As a result, the current passing through the sample increased in the absence of light. However, it was observed that the recovery of the current was slower than the initial decrease, indicating that the adsorption of oxygen molecules was a more challenging process compared to desorption.

In summary, under UV light irradiation, desorption of the ligand of the O₂ molecules from the MoO₃ surface releases electrons, which increases its carrier density. This led to decreased transport in the Ir layer due to Coulomb trapping and lowered hole mobility. While the carrier density in MoO₃ may increase, leading to potential enhancements in transport, the change in transport primarily depends on the behavior of the Ir layer within the heterostructure. Consequently, the decrease in transport observed in the Ir layer outweighs any potential increase in the level of MoO₃ transport. As a result, under light irradiation, the resistance of the heterostructure increases, ultimately leading to a decrease in the current flowing through the system.

Effect of Oxygen Vacancy. Nonetheless, the functioning of the MoO₃ device is impacted by elevated levels of bulk defects,^{64–67} leading to instabilities in the flat-band voltage. The presence of these defects becomes evident through several experimental methods, such as trap-assisted electron conduction involving the Poole–Frenkel mechanism,^{68–70} direct electron injection,⁷¹ and optical absorption.⁷² Although the specific energy levels of the defects vary across different experiments, the

oxygen vacancy is typically identified as their shared physical source.^{72–74} By this means, an oxygen vacancy has become interesting with direct contributions to optoelectronic conductivity.⁷⁵ A schematic diagram explaining the role of the oxygen vacancy in this MoO₃ structure is presented in Figure 9. The behavior of electrons is studied when they transition from the valence band to a defect level situated within the band gap of the material. This transition occurs when an electron absorbs a photon and gains enough energy to move from the lower energy valence band to the higher energy defect level. In the absence of light (Figure 9a), the MoO₃ sample exhibited distinct and well-defined crystal structures. However, upon subjecting the MoO₃ film to an annealing process in an air environment, an interesting phenomenon occurred. The MoO₃ film began to exhibit an increased presence of oxygen vacancies, as illustrated in Figure 9b. These oxygen vacancies arise due to the formation or desorption of lattice oxygen atoms,⁷⁶ resulting in the creation of trap states within the material. Then, when the MoO₃ sample is exposed to light, specifically under light illumination conditions, a notable transformation takes place; electrons in the valence band gain sufficient energy from the incident light and transition to the conduction band. As depicted in Figure 9c, these free electrons subsequently become captured by the existing oxygen vacancies within the material, which directly decrease the carrier mobility and increase the carrier concentrations to a large amount and consequently inverse the conductivity. The oxygen vacancies, acting as trapping sites, effectively capture and immobilize the free electrons, resulting in modified electronic behavior and the response of the MoO₃ film under illumination. These results confirm the Hall effect findings (Table 1) of presenting oxygen vacancy trap states and consequently produce the negative conductivity behavior of the PDs.

Response and Recovery Time. It is crucial to investigate how quickly the material can detect UV light without a bias voltage to gain a better understanding of the optoelectronic behavior of the ultrathin Ir layer during the annealing and post-annealing process. Upon ceasing UV light exposure, the signal starts to decay until it reaches the lowest dark current level, which indicates the recovery time. Figure 10 shows the measurements of the response and recovery time for the unannealed and post-annealed MoO₃/Ir/MoO₃/Si samples.

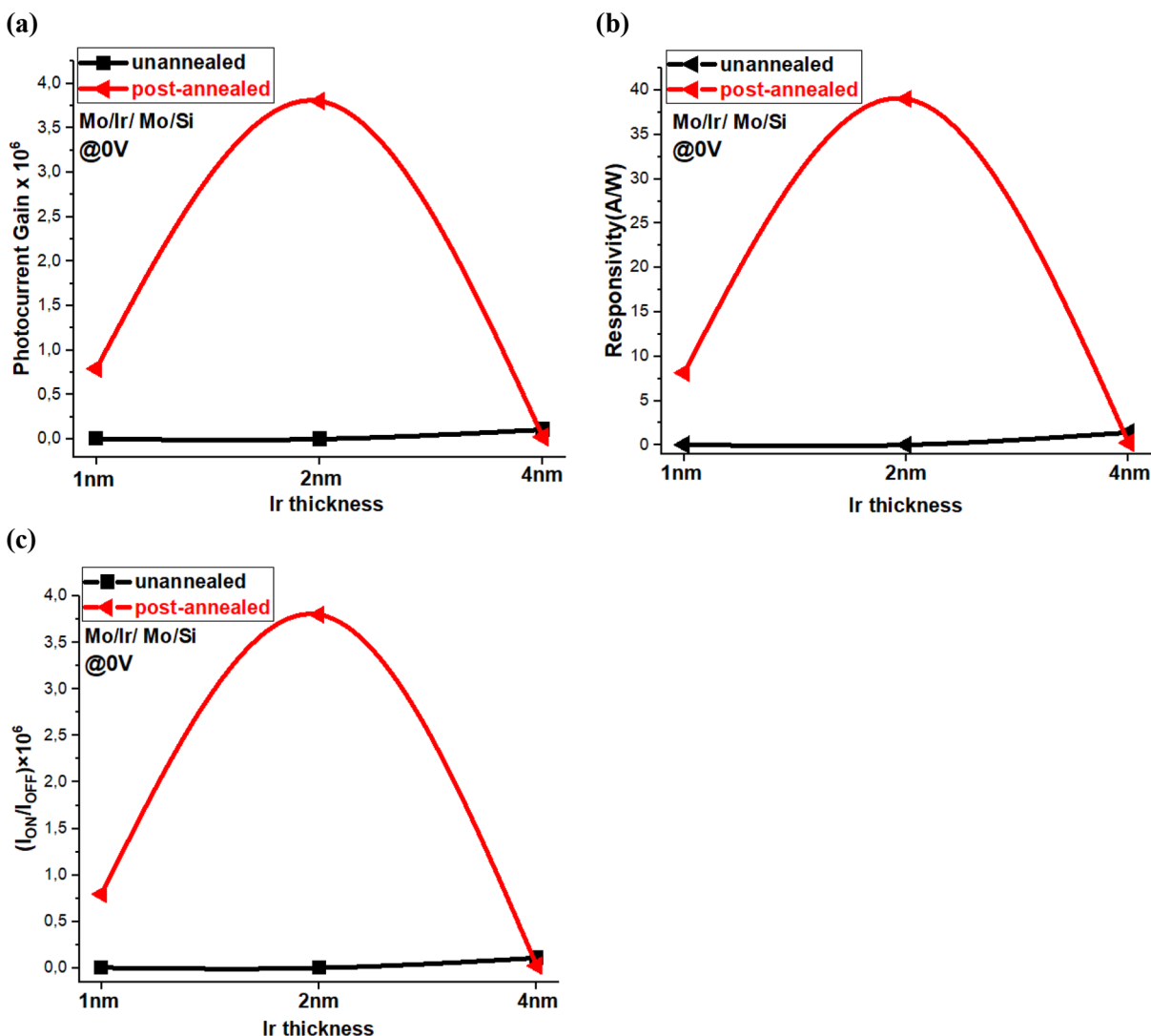


Figure 11. Photocurrent gain (a), responsivity (b), and the I_{ON}/I_{OFF} ratio (c) at 0 V of unannealed and post-annealed MoO₃/Ir/MoO₃/Si of different thicknesses of the Ir layer of 1, 2, and 4 nm.

Notably, all samples exhibit faster response times than recovery times. The post-annealed samples display a faster response time compared to the unannealed samples. This behavior can be attributed to the annealing process, which improves the crystallinity of the film and enhances the fast electron transfer process. The response time of the postannealed samples is approximately 0.2 ms for the 2 nm Ir sample, with a slight increase toward the 1 and 4 nm Ir layer. In contrast, the response time for the unannealed samples reached 1 ms. Furthermore, the recovery time of the postannealed samples reaches its lowest value at the 2 nm Ir layer, measuring 0.33 ms. In contrast, the unannealed samples require a slightly longer time of 0.41 ms for the 2 nm Ir sample to recover. This observation may be due to the postannealing process's ability to enhance the material's crystallinity, which helps facilitate carrier transport, thus reducing the recovery time.

The plasmonics of the Ir layer play a crucial role in enhancing the performance of the UV PD. When the Ir layer is exposed to UV light, it generates excited electrons that are transferred to the metal layer's surface, leading to the excitation of plasmons. Plasmons are collective oscillations of free electrons in a metal that generate an enhanced electromagnetic field around the

metal surface. This increased field creates a higher local density of optical states, which can enhance the absorption of the UV light. The increased absorption of UV light due to plasmonics leads to a significant increase in the photocurrent generated by the PD. The increased photocurrent results in a faster response time, as more carriers are generated and transferred through the device. This enhanced response time is particularly important in applications where the rapid detection of UV light is required. Moreover, plasmons can also assist in reducing the recovery time of PD. After the UV light is removed, the excited holes relax, which is a slow process that limits the PD's response speed. However, the plasmons can accelerate the carrier mobility process by enhancing the local density of states around the metal surface and thus reducing the recovery time of the PD.

Overall, these findings indicate that post-annealing the ultrathin Ir layer can significantly improve the material's optoelectronic properties, resulting in faster response and recovery times. Additionally, the results suggest that the thickness of the Ir layer plays a role in determining the material's response and recovery times, whereas a thinner layer has a faster response and recovery time. By this means, the plasmonics of the Ir layer can significantly enhance the performance of the UV PD

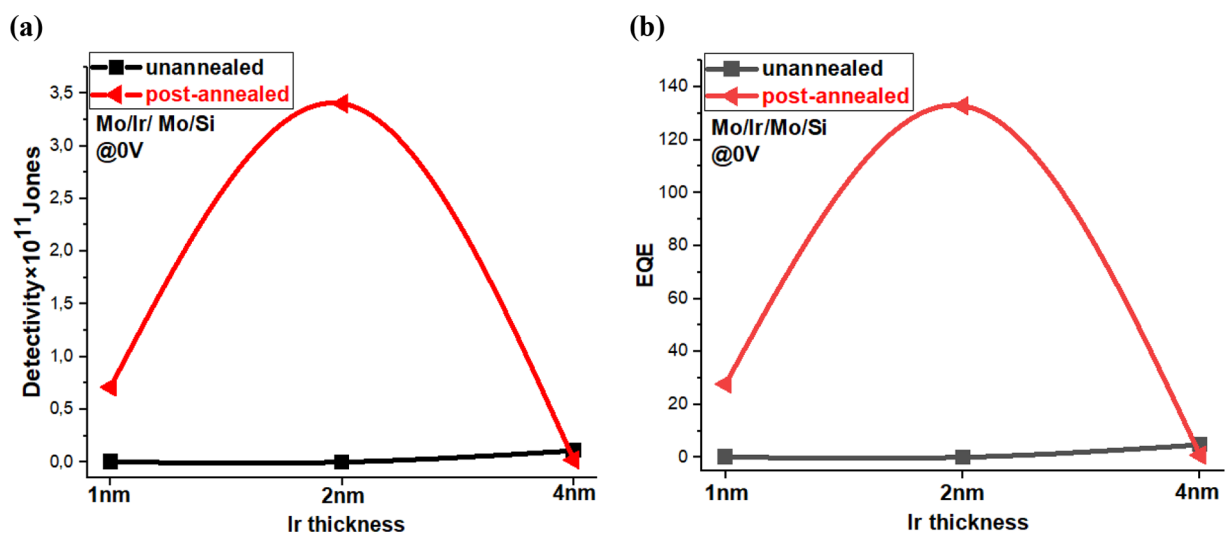


Figure 12. Detectivity (a) and EQE (b) at 0 V of unannealed and post-annealed MoO₃/Ir/MoO₃/Si with different thicknesses of the Ir layer of 1, 2, and 4 nm.

by increasing the absorption of UV light and increasing the carrier concentrations. The improved response and recovery times achieved through plasmonics can make the UV PD more suitable for applications requiring the rapid and sensitive detection of UV light.

Photocurrent Gain and Responsivity. Figure 11 presents a detailed analysis of the optoelectronic properties of MoO₃/Ir/MoO₃/Si structures with varying thicknesses of the Ir layer (1, 2, and 4 nm). The figure provides information on the photocurrent gain, responsivity, and the $I_{\text{ON}}/I_{\text{OFF}}$ ratio at 0 V for both unannealed and post-annealed samples. In Figure 11a, the photocurrent gain for each Ir layer thickness is shown. It is observed that the 1 and 2 nm Ir layers exhibit higher photocurrent gains compared to the 4 nm Ir layer, especially undergoing the post-annealing process, indicating their superior ability to generate photocurrents in response to external illumination. The post-annealed MoO₃/2 nm Ir/MoO₃/Si sample demonstrates the highest value among the tested samples, reaching 3.8E6, when evaluated as a self-powered PD. This result indicates that the MoO₃/2 nm Ir/MoO₃/Si structure, after undergoing the post-annealing process, exhibits remarkable performance in converting incident light into electrical signals without requiring an external power source. The high value of 3.8E6 signifies a significantly amplified photocurrent response to incident light. This suggests that the MoO₃/2 nm Ir/MoO₃/Si sample efficiently captures photons and converts them into electrical currents, making it an excellent candidate for self-powered PD applications.

Figure 11b displays the responsivity at 0 V of the MoO₃/Ir/MoO₃/Si structures with different Ir layer thicknesses. Figure S6 (Supporting Information) shows the responsivity as a function of voltages of 0, 0.5, 1, 2, 3, 4, and 5 V for unannealed and post-annealed MoO₃/Ir/MoO₃/Si thin films at a UV 365 nm wavelength light source. The responsivity values reflect how efficiently the devices convert incident light into electrical signals. The results indicate that the 2 nm Ir layer exhibits a higher responsivity of 39 A/W compared to both the 1 and 4 nm Ir layers. This suggests that the 2 nm Ir layer is more sensitive to light and produces stronger electrical responses when subjected to a 0 V bias under the post-annealing process. The observed behavior aligns with the trend observed in the photocurrent

gain, further supporting the notion that the thickness of the Ir layer influences the device's light sensitivity and electrical response. The higher responsivity of the 2 nm Ir layer indicates its ability to more efficiently convert incident light into electrical signals, making it a favorable choice for optoelectronic applications requiring enhanced light detection capabilities. In Figure 11c, the $I_{\text{ON}}/I_{\text{OFF}}$ ratio at 0 V is presented, which measures the device's ability to switch between the ON and OFF states. A higher $I_{\text{ON}}/I_{\text{OFF}}$ ratio indicates a more distinct differentiation between these states. The data reveal that the 2 nm Ir layer exhibits a higher $I_{\text{ON}}/I_{\text{OFF}}$ ratios of 3.8×10^6 compared to both the 1 and 4 nm Ir layers. This indicates that the 2 nm Ir layer possesses superior switching capabilities compared with the other two thicknesses. The higher $I_{\text{ON}}/I_{\text{OFF}}$ ratio of 3.8×10^6 for the 2 nm Ir layer signifies a more pronounced distinction between the ON and OFF states of the device. Importantly, the achieved $I_{\text{ON}}/I_{\text{OFF}}$ ratio of 3.8×10^6 for the 2 nm Ir layer surpasses values reported in existing literature reviews. This highlights the notable performance of the 2 nm Ir layer in terms of its switching characteristics, demonstrating its potential for advancement in optoelectronic devices and surpassing previously reported results. The observed improvements in photocurrent gain, responsivity, and $I_{\text{ON}}/I_{\text{OFF}}$ ratio in the postannealed samples of the MoO₃/Ir/MoO₃/Si structures can be attributed to several factors. The postannealing process enhances the crystalline structure, reducing defects and improving charge transport properties. It also promotes better interface formation between the layers, enhancing the efficiency of charge transfer and increasing responsivity. Additionally, post-annealing optimizes the doping and carrier concentration profiles, reducing leakage current and improving the $I_{\text{ON}}/I_{\text{OFF}}$ ratio.

Detectivity and EQE. In Figure 12, the detectivity and EQE at 0 V are presented for both unannealed and postannealed MoO₃/Ir/MoO₃/Si samples with varying thicknesses of the Ir layer (1, 2, and 4 nm). The detectivity measurement provides valuable insights into the sensitivity and noise performance of the PDs, while the EQE measurement indicates the efficiency of converting incident photons into electrical currents. These measurements play a pivotal role in optimizing device design, material selection, and fabrication processes to enhance

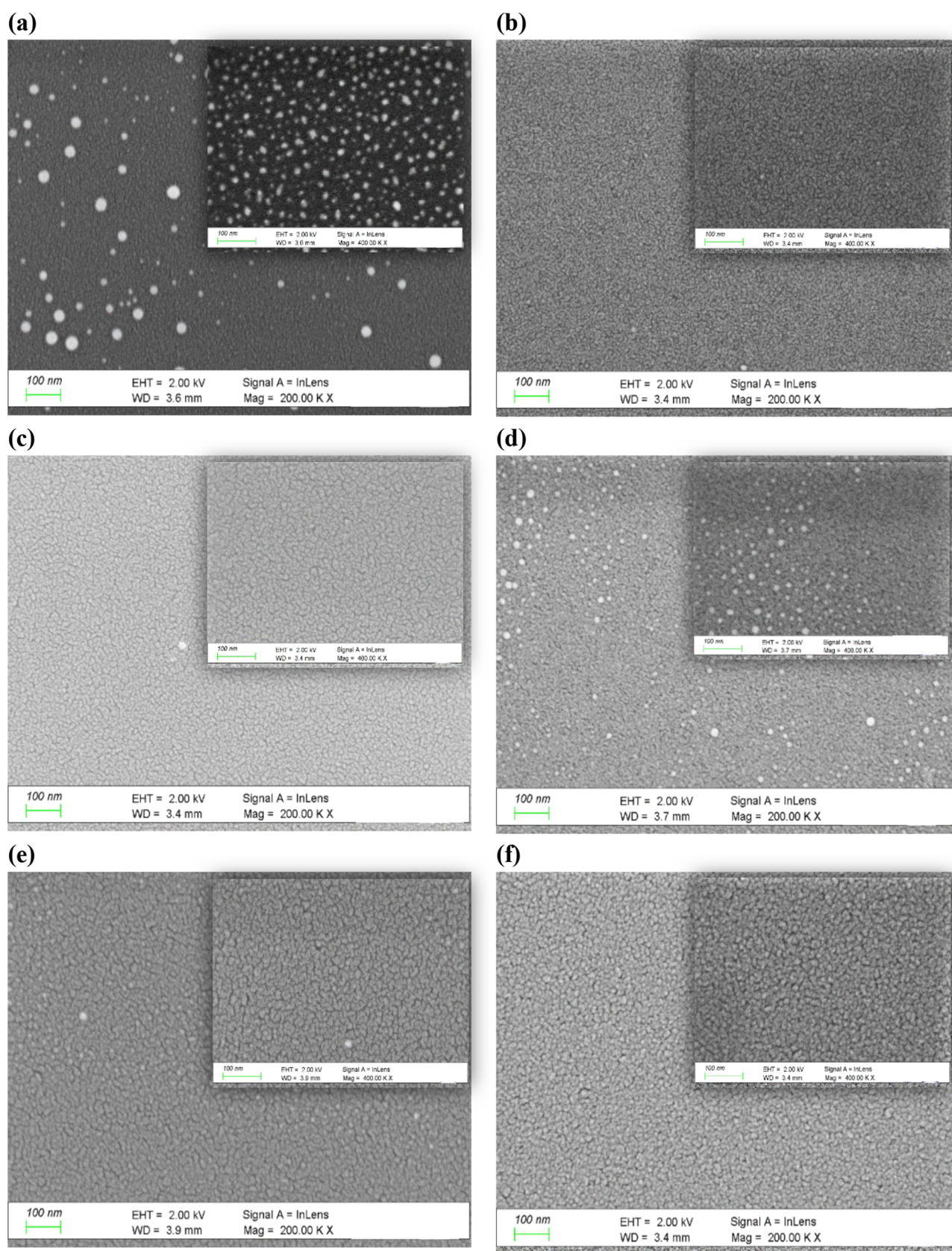


Figure 13. Surface morphology of unannealed MoO₃/Ir/MoO₃/Si (a–c) and postannealed (d–f) samples with different Ir thicknesses of 1, 2, and 4 nm respectively as observed under FESEM at different magnifications of 200 and 400 KX (inset).

performance and expand the range of applications for self-powered UV PDs. Detectivity (Figure 12a) provides a

quantifiable measure of sensitivity by evaluating the device's ability to distinguish the desired UV signal from background

Table 2. Elemental Composition of Unannealed and Post-annealed MoO₃/Ir/MoO₃/Si Samples, While the Concentrations of All Elements Are Recorded in wt %

samples	presence of Si				absence of Si			
	Si	O	Ir	Mo	O	Ir	Mo	
unannealed	MoO ₃ /1 nm Ir/MoO ₃ /Si	97.0	1.5	1.2	0.4	40.0	50.4	9.6
	MoO ₃ /2 nm Ir/MoO ₃ /Si	94.9	1.7	2.7	0.7	28.5	63.1	8.5
	MoO ₃ /4 nm Ir/MoO ₃ /Si	93.2	1.9	4.1	0.8	24.3	24.3	6.7
post-annealed	MoO ₃ /1 nm Ir/MoO ₃ /Si	97.0	1.7	1.2	0.1	44.5	53.0	2.5
	MoO ₃ /2 nm Ir/MoO ₃ /Si	95.6	2.1	2.2	0.1	39.1	60.2	0.7
	MoO ₃ /4 nm Ir/MoO ₃ /Si	93.5	2.4	3.9	0.2	30.4	69.6	0.0

noise. Higher detectivity values, as observed for the post-annealed 2 nm Ir layer, indicate superior sensitivity and the capacity to detect weak UV signals while maintaining signal integrity amid the noise. The postannealed MoO₃/2 nm Ir/MoO₃/Si sample demonstrates an impressive detectivity value of 3.4×10^{11} Jones at 0 V bias. This high detectivity indicates the PD's exceptional sensitivity and ability to detect weak UV signals while minimizing the impact of background noise. The post-annealing process significantly contributes to achieving such a high detectivity by improving the crystalline structure, enhancing the quality of interfaces between layers, and optimizing overall device performance. These improvements effectively reduce noise levels, thereby increasing the signal-to-noise ratio and enabling the detection of even subtle UV signals with remarkable accuracy and reliability. The observed detectivity value of 3.4×10^{11} Jones underscores the outstanding performance of the post-annealed MoO₃/2 nm Ir/MoO₃/Si sample, highlighting its potential for demanding applications that require highly sensitive and efficient self-powered UV PD.

A higher EQE value (Figure 12b), such as the observed value of 132 for the post-annealed MoO₃/2 nm Ir/MoO₃/Si sample, indicates improved conversion efficiency and optimal utilization of incident UV light. This means that a larger proportion of incident UV photons is effectively converted into usable electrical current. Achieving a higher EQE value is crucial for high-performance self-powered UV PD as it ensures that a greater number of photons is successfully converted into electrical signals. This signifies excellent light absorption and charge generation capabilities in the device. By maximizing the utilization of incident UV light, the post-annealed MoO₃/2 nm Ir/MoO₃/Si sample demonstrates enhanced efficiency in capturing and utilizing the available light energy, resulting in a stronger and more reliable electrical output signal. The higher EQE value of 132 highlights the sample's exceptional performance in converting incident UV photons into usable electrical current, making it well-suited for demanding self-powered UV PD applications.

Surface Morphology and Elemental Composition.

Figure 13a–c shows the FESEM of unannealed MoO₃/Ir/MoO₃/Si samples at 200 and 400 KX different magnifications of samples of MoO₃/1 nm Ir/MoO₃/Si, MoO₃/2 nm Ir/MoO₃/Si, and MoO₃/4 nm Ir/MoO₃/Si samples, respectively. For this case, at 1 nm Ir thickness, bigger particles are observed at low magnifications and increased at high magnifications. Those particles can be attributed to high distortion and scattering of the incident light and consequently will decrease the PD performances, as shown above in the electrical and optoelectronics sections. However, with increasing the thickness for 2 nm Ir, small porous structures started to appear. A similar case is observed at the 4 nm case with more porosity and more Ir content of 4 nm. In the 4 nm thickness, the conductivity

increases dramatically, followed by 2 nm and then 1 nm cases. These results confirm the high optoelectronic properties of 4 nm Ir thick film.

The EQE, D^* , responsivity, and response time values of 1 and 2 nm are somehow near each other. For the post-annealed MoO₃/Ir/MoO₃/Si samples with 1, 2, and 4 nm Ir thickness at different magnifications, the FESEM images are reported in Figure 13d–f. It is observed that the particles are a bit larger and denser after the postannealing process. At the same time, smoothing and homogeneity are presented here as well. Some very small particles are observed here, which are related to some agglomerations from the ALD tube lines that are related to MoO₃ particles. By comparing the unannealed and post-annealed samples for both groups, we can get an idea related to the effect of annealing on the morphological images. It is observed that for the unannealed MoO₃/1 nm Ir/MoO₃/Si, some particles are presented, but after the postannealed, these particles are enhanced and become smoother. This effect could directly affect the conductivity and optoelectronic properties, as shown from the optoelectronics measurements. The surface morphology of a PD can have a significant effect on its performance. The surface morphology can affect the absorption and scattering of light, the charge transport properties, and the surface photogenerated carrier concentrations. However, for the MoO₃/2 nm Ir/MoO₃/Si samples, we can observe small particles for both cases of unannealed and postannealed cases.

EDS analysis of the unannealed and post-annealed samples here is interesting as well to look at any changes in the composition and structures, as shown in Table 2. For the unannealed MoO₃/1, 2, and 4 nm Ir/MoO₃/Si, it is important to highlight that all the deposited MoO₃ layer is based on the same conditions in all Ir-based samples. The amount of Mo is 0.4, 0.7, and 0.8%; this increment is usually to balance the total amount of 100%. The Ir amounts are 1.2, 2.7, and 4.1%, as usual, because the deposited thickness is increased from 1, 2, and 4 nm over the whole surface. Moreover, for the O case, it is found 1.5, 1.7, and 1.9%. These results in the presence of Si peaks are normal, as expected before for the other samples. However, in the absence of a Si peak, the results show that Mo has 9.6, 8.5, and 6.7, which is decreasing logically as the Ir concentrations are increasing by 50.4, 63.1, and 69.0% for the O concentrations 40.0, 28.5, and 24.3%. On the other hand, for the post-annealed MoO₃/Ir/MoO₃/Si with 1, 2, and 4 nm Ir thickness, it is also interesting to look at the elemental analysis. First, in the presence of Si peaks, the Mo concentrations are almost the same at 0.1, 0.1, and 0.2%. The Ir contents are about 1.2, 2.2, and 3.9%. It may refer to these results, which enhanced the presence and crystallinity of MoO₃/Ir layer/MoO₃ for better PD performance. For the O contents, 1.7, 2.1, and 2.4%. On the other hand, by looking at the concentrations of these elements of the unannealed MoO₃/Ir/MoO₃/Si samples, we found that the detected amount of Mo

Table 3. Roughness Measurement of Unannealed and Post-annealed MoO₃/Ir/MoO₃/Si with 1, 2, and 4 nm Ir Thickness^a

	sample	min (nm)	max (nm)	mid (nm)	R _{pv} (nm)	R _q (nm)	R _z (nm)	R _z (nm)	R _{sk}	R _{ku}
unannealed	MoO ₃ /1 nmIr/MoO ₃ /Si	-0.57	0.44	-0.06	1.01	0.19	0.16	0.79	0.23	2.66
	MoO ₃ /2 nmIr/MoO ₃ /Si	-0.89	0.80	-0.04	1.69	0.32	0.25	1.33	-0.03	3.04
	MoO ₃ /4 nmIr/MoO ₃ /Si	-4.39	4.52	0.07	8.91	2.22	1.81	8.59	-0.21	2.29
post-annealed	MoO ₃ /1 nmIr/MoO ₃ /Si	-1.43	1.20	-0.12	2.64	0.54	0.43	2.28	0.01	2.57
	MoO ₃ /2 nmIr/MoO ₃ /Si	-0.75	1.21	0.22	1.98	0.35	0.28	1.29	-0.25	3.13
	MoO ₃ /4 nmIr/MoO ₃ /Si	-6.68	6.53	-0.08	13.21	3.26	2.63	12.13	0.087	2.21

^aThe measurements were taken through a horizontal line.

was 0.4, 0.7, and 0.8%, the Ir was 1.2, 2.7, and 4.1%, and finally, the O amounts were 1.5, 1.7, and 1.9%. Comparing the results of the unannealed and the post-annealed samples, we found that the concentration of Mo decreased, Ir decreased, and O increased, the excess of the oxidation of the Si substrate. On the other hand, in the absence of Si peaks, Mo is 2.5, 0.7, and 0%, Ir is 53.0, 60.2, and 69.6%, and O is 44.5, 39.1, and 30.4%. The contents of Mo decreased, Ir increased, and the contents of O decreased.

Surface Topography and Roughness. In the field of surface metrology and topography, various parameters are utilized to characterize the topography of a surface. These parameters offer valuable insights into the surface's features and irregularities. One such parameter is the average roughness (R_a) that represents the arithmetic mean of surface heights within a defined area. It provides a measure of the overall surface roughness. The root means square of the height values (R_q) is another parameter that quantifies the deviation of height values from the mean, indicating the surface's overall variation. The height difference or peak-to-valley distance (R_{pv}) measures the vertical span between the highest peak and the lowest valley on the surface, reflecting the extent of surface irregularities. Additionally, the ten-point height (R_z) parameter is used to calculate the average height of the five highest peaks and the five lowest valleys on the surface, providing a measure of localized surface features. Furthermore, parameters such as skewness (R_{sk}) and kurtosis (R_{ku}) describe the asymmetry and sharpness of the surface features, respectively. These parameters collectively provide a comprehensive description of the surface topography, facilitating quantitative analysis and comparison. A summary of these parameters for both annealed and post-annealed samples can be found in Table 3, while the 3D images are presented in Figures S4 and S5 (Supporting Information). The AFM analysis of the unannealed and post-annealed MoO₃/Ir/MoO₃/Si samples provides valuable insights into their surface characteristics. A comparison between the two chromatographs reveals notable differences. The post-annealed samples exhibit slightly higher values for R_{pv} , R_q , and R_a compared to the unannealed samples, suggesting surface modifications induced by the annealing process and increased roughness. However, despite the increase in roughness, the post-annealed samples demonstrate improved performance as high-performance PDs. This suggests that factors beyond surface roughness, such as interface quality, defect reduction, and carrier transport, are crucial to determining PD performance. It is important to note that even with the slight increase in roughness, the post-annealed samples show significant enhancements in detectivity and EQE values. For instance, the MoO₃/2 nm Ir/MoO₃/Si sample exhibits a detectivity value of 3.4×10^{11} Jones and an EQE value of 132 at 0 V bias. These findings highlight the importance of optimizing various parameters to achieve high-performance self-powered PD. Interestingly, Table S2 (Support-

ing Information) shows the AFM surface topography parameters of the Ir/Si device of 1, 2, and 4 nm Ir layer. Notably, the 1 nm Ir sample exhibited the lowest roughness of 0.29 nm, indicating a highly smooth and uniform surface.

CONCLUSIONS

In conclusion, this study investigates the performance of self-powered photodetectors based on α -MoO₃/Ir/ α -MoO₃ structures after post-annealing. The annealing process significantly improves optoelectronic properties, enabling negative photoconductivity at a 0 V bias voltage. Notably, this study demonstrates the first instance of a MoO₃-based UV photodetector exhibiting a negative response with higher detectivity compared to the unannealed counterpart. The device achieves a rapid 0.2 ms response time at a 0 V bias, highlighting its suitability for high-speed applications. Furthermore, the study reveals the superior performance of 1 and 2 nm Ir layers in terms of photocurrent generation, light sensitivity, and switching behavior, while the 4 nm Ir layer exhibits weaker performance. The interplay between different layers in the MoO₃/Ir/MoO₃ structures and the role of oxygen vacancies are elucidated, with the oxygen vacancies acting as trap-assisted conduction centers that reduce carrier density and lead to negative photoconductivity. These findings highlight the potential of nanostructured MoO₃/Ir heterostructures for high-performance self-powered photodetectors, contributing to advancements in transparent optoelectronics, integrated photonic systems, and energy harvesting technologies.

ASSOCIATED CONTENT

Data Availability Statement

The data presented in this study can be obtained upon request from the corresponding author.

Supporting Information

The Supporting Information is available free of charge at <https://pubs.acs.org/doi/10.1021/acsaelm.3c01047>.

Additional experimental details for enhanced photodetector performance and characterization.

Supplementary figures and tables for a deeper understanding of the study.

Figure S1: comparative OFF-ON performance of both unannealed and postannealed MoO₃/Ir/MoO₃/Si photodetectors across bias voltages of 0, 0.5, 1, 2, 3, 4, and 5 V; Figure S2: assessment of mobility and carrier concentration in unannealed and postannealed MoO₃/Ir/MoO₃/Si samples; Figure S3: diffuse reflectance measurements for unannealed and post-annealed MoO₃/Ir/MoO₃/Si samples; Figure S4: three-dimensional topography depiction along with line profiles of the unannealed MoO₃/Ir/MoO₃/Si device; Figure S5: three-dimensional topography visualization along with

line profiles of the post-annealed MoO₃/Ir/MoO₃/Si device; figure S6: responsivity as a function of applied bias voltages of 0, 0.5, 1, 2, 3, 4, and 5 V for unannealed and post-annealed MoO₃/Ir/MoO₃/Si thin films under a UV 365 nm wavelength light source; Table S1: compilation of electrical Hall effect measurements for Ir/Si samples with 1, 2, and 4 nm Ir layers; Table S2: AFM surface topographical parameters of Ir/Si device with 1, 2, and 4 nm Ir layers (PDF)

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Notes

The authors declare no competing financial interest.

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